

## Features

- Uses PingWei advanced PerfectMOS2 technology
- Extremely low on-resistance  $R_{DS(on)}$
- Excellent  $Q_g \times R_{DS(on)}$  product(FOM)
- Excellent Low Ciss
- 175°C operating temperature
- Top Side Cooling
- Qualified according to AEC-Q101 criteria

## Applications

- General automotive applications

## Benefits

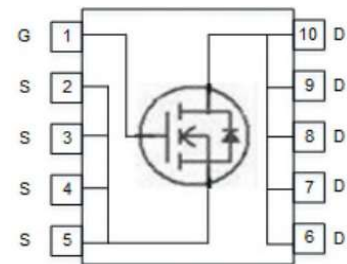
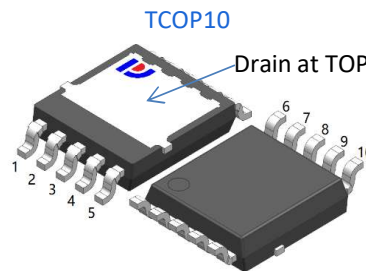
- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Easy paralleling



**100% DVDS Tested**  
**100% Avalanche Tested**

## Product Summary

$V_{DS}$	40V
$R_{DS(on)}@10V$ typ	0.64mΩ
$I_D$ (silicon limit)	357A



Pins 10 - 6 & Tab on Drain

## Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PWTC008N04PSQ	PWTC0804	TCOP10	Tape&Reel	13 inches	16mm	3000pcs

## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	40	V
Continuous drain current	$I_D$	357	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		175	
$T_C = 25^\circ\text{C}$ (Package limit)		252	
Pulsed drain current ( $T_C = 25^\circ\text{C}, tp=100\mu\text{s}$ )	$I_{D\ pulse}$	1381	A
Avalanche energy, single pulse ( $L=0.1\text{mH}$ )	$E_{AS}$	420	mJ
Gate-Source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation	$P_{tot}$	197	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+175	$^\circ\text{C}$
Reflow soldering temperature (10s)	$T_{sold}$	260	$^\circ\text{C}$

## Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction - case.	RthJC	-	-	0.76	°C/W	Junction to TOP Tab
Thermal resistance, junction - ambient	RthJA	-	-	57	°C/W	1 inch <sup>2</sup> , 2oz single copper FR-4 PCB

## Electrical Characteristic (at T<sub>j</sub> = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

## Static Characteristic

Drain-source breakdown voltage	BV <sub>DSS</sub>	40	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Gate threshold voltage	V <sub>GS(th)</sub>	2.0	-	3.5	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	1 100	μA	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V T <sub>j</sub> =25°C T <sub>j</sub> =125°C
Gate-source leakage current	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source on-state resistance	R <sub>DS(on)</sub>	-	0.64	0.79	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =30A
Transconductance	g <sub>fs</sub>	-	120	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =30A

## Dynamic Characteristic

Input Capacitance	C <sub>iss</sub>	-	6895	10342	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =20V, f=100KHz
Output Capacitance	C <sub>oss</sub>	-	2394	3590		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	73	147		
Gate Total Charge	Q <sub>G</sub>	-	94	127	nC	V <sub>DS</sub> =20V, I <sub>D</sub> =30A, V <sub>GS</sub> =10V
Gate-Source charge	Q <sub>gs</sub>	-	29	44		
Gate-Drain charge	Q <sub>gd</sub>	-	13	25		
Turn-on delay time	t <sub>d(on)</sub>	-	19	-	ns	V <sub>GS</sub> =10V, V <sub>DD</sub> =20V, R <sub>G_ext</sub> =1.6Ω, I <sub>D</sub> =20A
Rise time	t <sub>r</sub>	-	35	-		
Turn-off delay time	t <sub>d(off)</sub>	-	66	-		
Fall time	t <sub>f</sub>	-	20	-		
Gate resistance	R <sub>G</sub>	-	2.9	-	Ω	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz

## Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	$V_{SD}$	-	-	1.2	V	$V_{GS}=0V, I_{SD}=30A$
Body Diode Continuous Forward Current	$I_S$	-	-	175	A	TC = 25°C
Body Diode Pulsed Current	$I_S$ pulse	-	-	1381	A	TC = 25°C, $t_p=100\mu s$
Body Diode Reverse Recovery Time	$t_{rr}$	-	50	-	ns	$I_F=50A,$ $dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{rr}$	-	53	-	nC	

## Typical Performance Characteristics

Fig 1: Output Characteristics

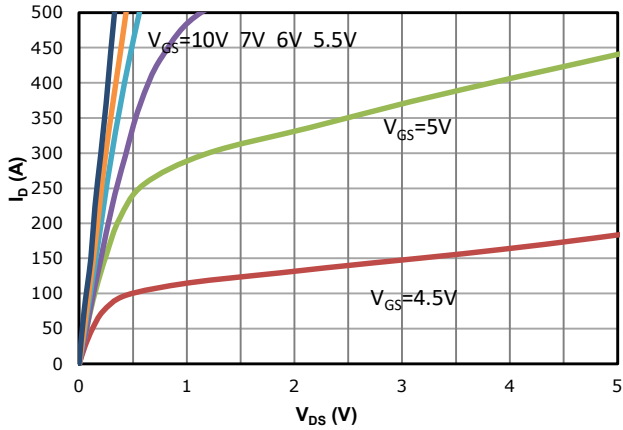


Fig 2: Transfer Characteristics

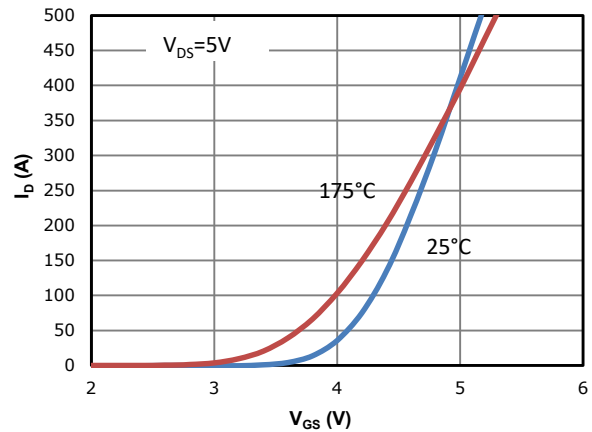


Fig 3:  $R_{DS(on)}$  vs Drain Current and Gate Voltage

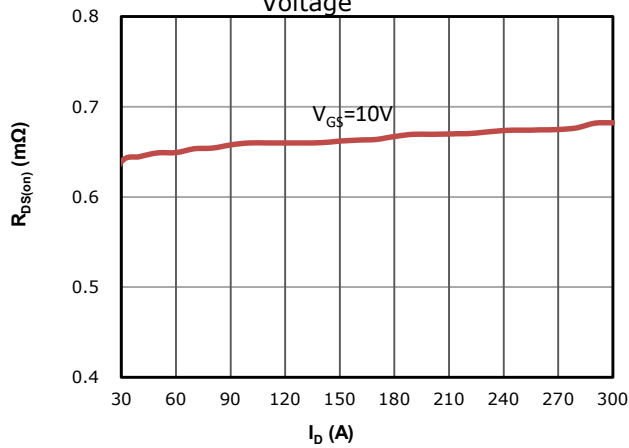


Fig 4:  $R_{DS(on)}$  vs Gate Voltage

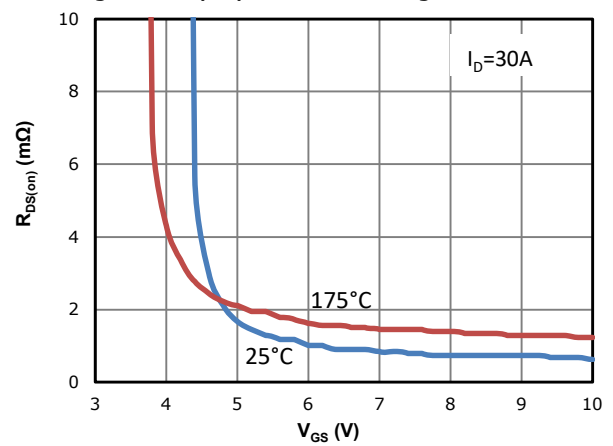


Fig 5:  $R_{DS(on)}$  vs. Temperature

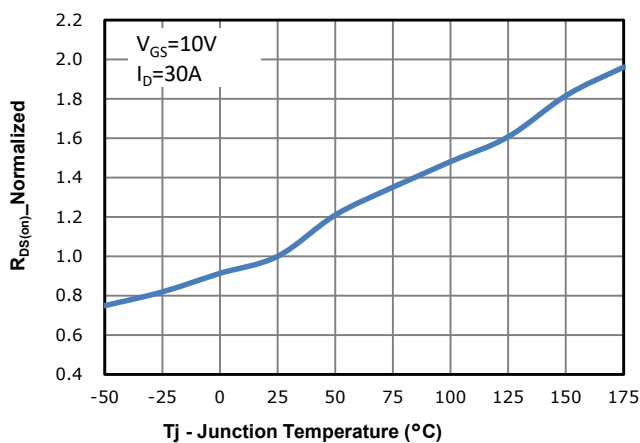


Fig 6:  $V_{GS(th)}$  vs. Temperature

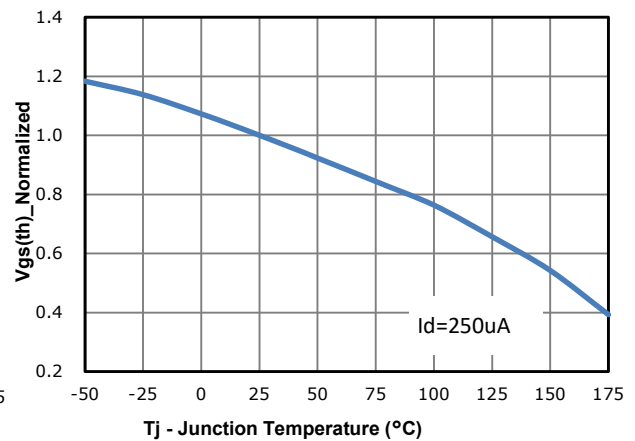


Fig 7: BVdss vs. Temperature

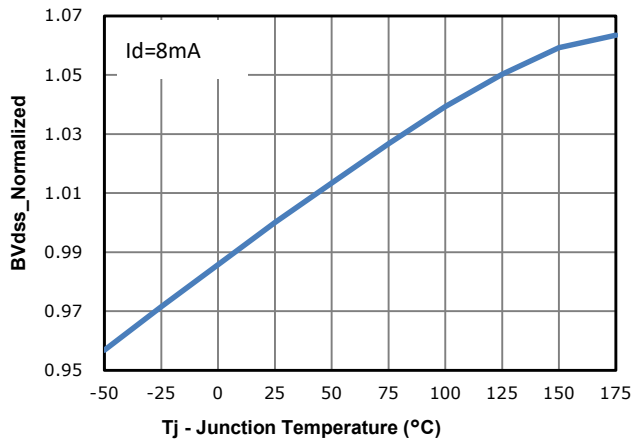


Fig 8: Capacitance Characteristics

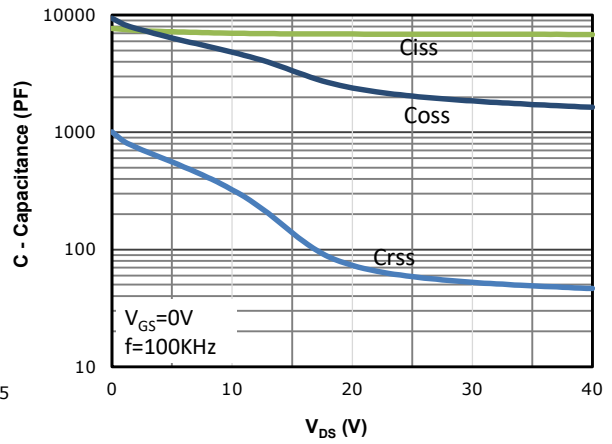


Fig 9: Gate Charge Characteristics

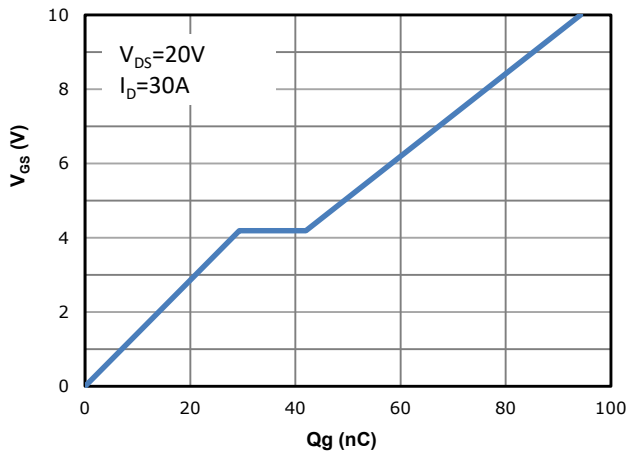


Fig 10: Body-diode Forward Characteristics

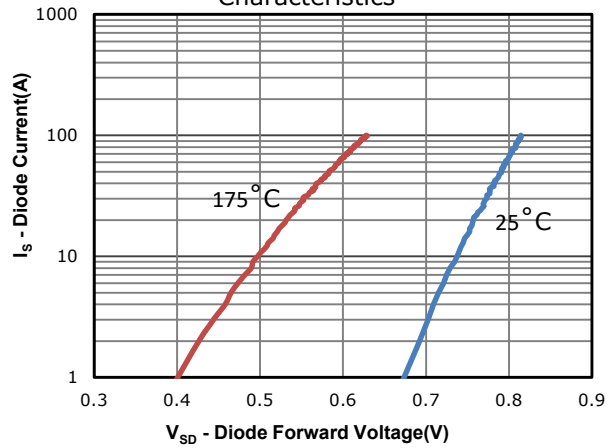


Fig 11: Power Dissipation

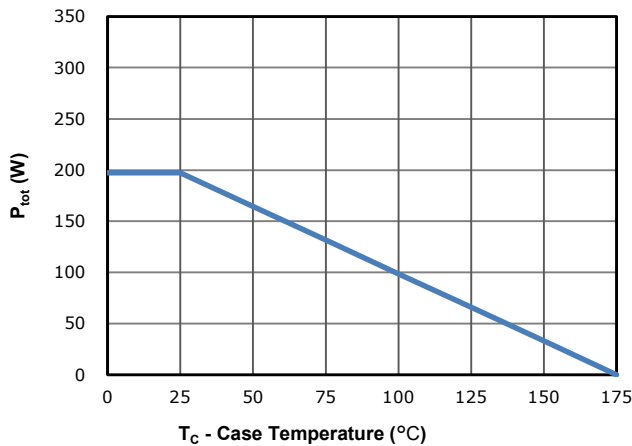


Fig 12: Drain Current Derating

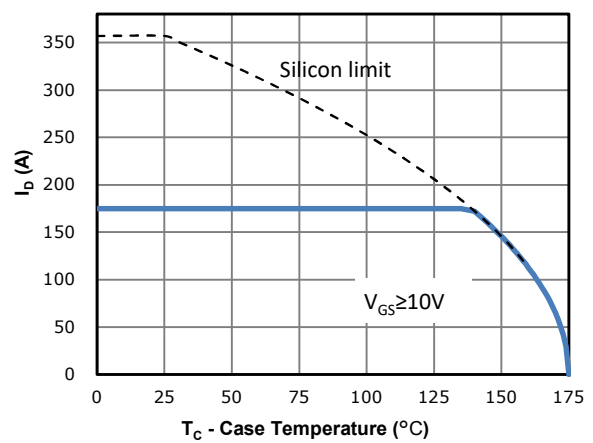


Fig 13: Safe Operating Area

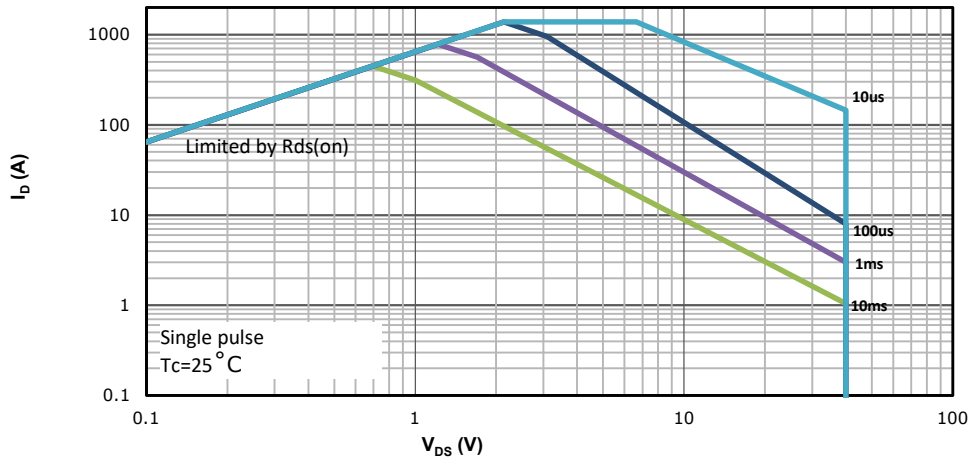
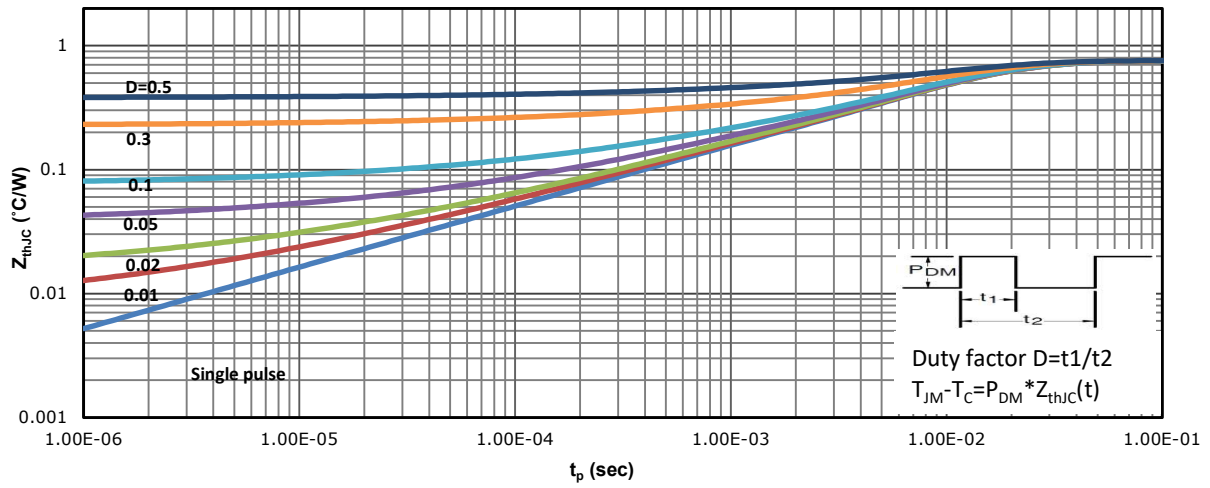
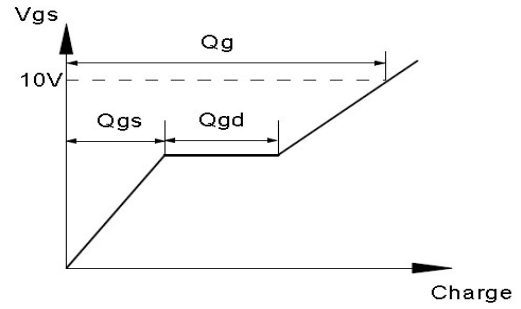
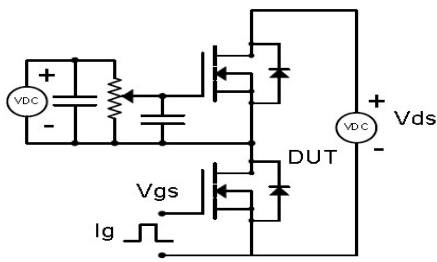


Fig 14: Max. Transient Thermal Impedance

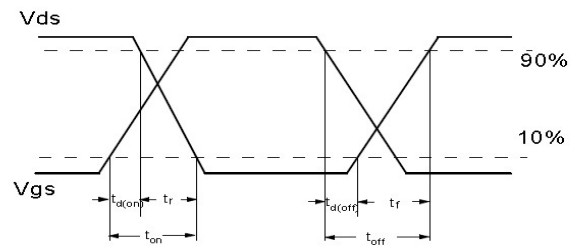
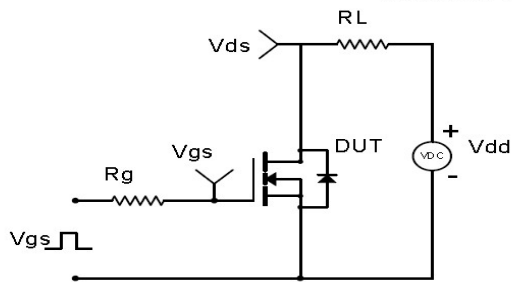


## Test Circuit & Waveform

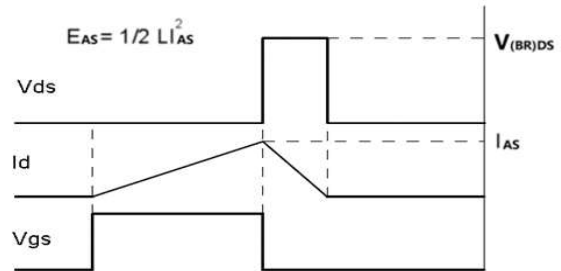
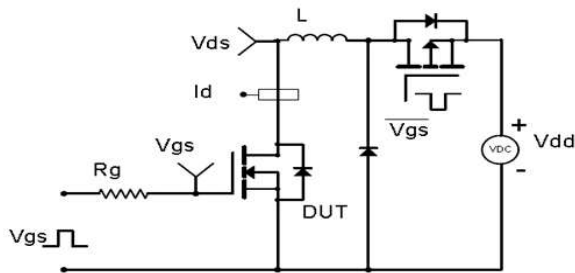
Gate Charge Test Circuit & Waveform



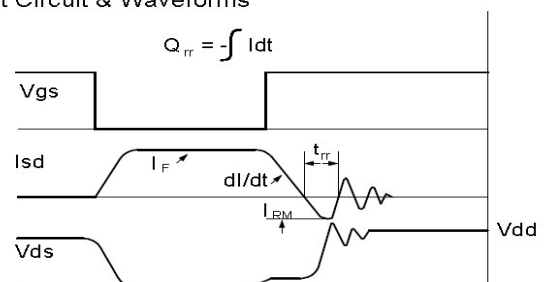
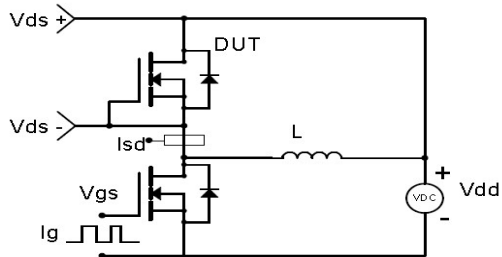
Resistive Switching Test Circuit & Waveforms



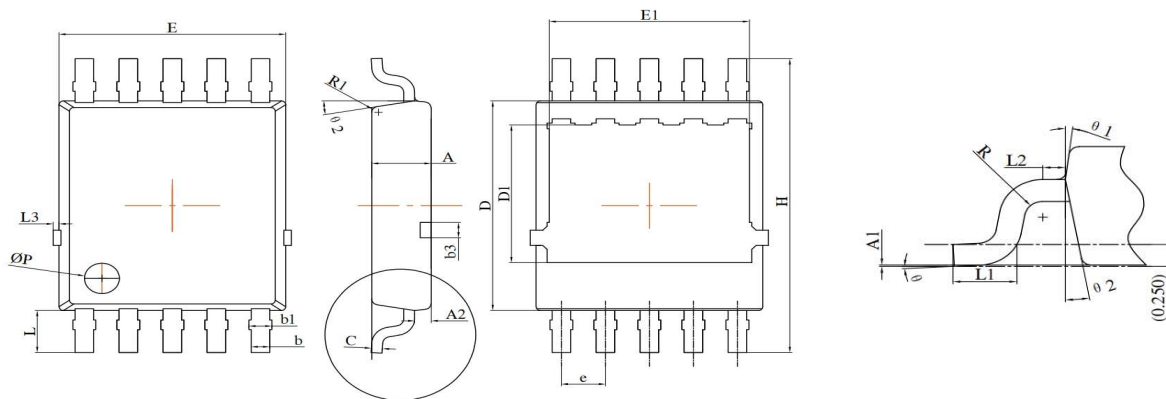
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



## Package Outline: TCOP10



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.25	1.45	0.049	0.057
A1	0.00	0.10	0.000	0.004
A2	0.275	0.475	0.011	0.019
b	0.32	0.52	0.013	0.020
b1	0.37	0.67	0.015	0.026
c	0.20	0.30	0.008	0.012
D	5.33	5.63	0.210	0.222
D1	3.45	3.75	0.136	0.148
E	5.05	5.25	0.199	0.207
E1	4.30	4.80	0.169	0.189
e	1.00bsc		1.00bsc	
H	7.48	7.88	0.294	0.310
L	0.95	1.25	0.037	0.049
L1	0.50	0.80	0.020	0.031
L2	0.16	0.36	0.006	0.014
L3	0.00	0.15	0.000	0.006
P	0.85	1.15	0.033	0.045
R	0.10	0.28	0.004	0.011
R1	0.10	0.25	0.004	0.010
θ	0°	6°	0°	6°
θ1	5°	9°	5°	9°
θ2	8°	12°	8°	12°



## Revision History

Revision	Date	Major changes
2.1	2026/2/2	Update Package limit ID from 120A to 175A;Tighten Qg spec;

## Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

The product is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation/aerospace and life-support devices or systems.

Buyer is responsible for its products and applications using PingWei products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by PingWei.

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